Ordering number : ENN8189A

SANYO Semiconductors
DATA SHEET

N-Channel Silicon MOSFET

FTS2051 — General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.
- Mounting height 1.1mm.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		4.5	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	18	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (1000mm²×0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	1.2		2.6	V
Forward Transfer Admittance	$\|yfs\|$	V_{DS}=10V, I_D=3A	2.7	4.5		S
Static Drain-to-Source On-State Resistance	R_{DS}(on) 1	I_D=3A, V_{GS}=10V		42	55	mΩ
	R_{DS}(on) 2	I_D=1.5A, V_{GS}=4V		66	90	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		460		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		95		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		75		pF

Marking : S2051

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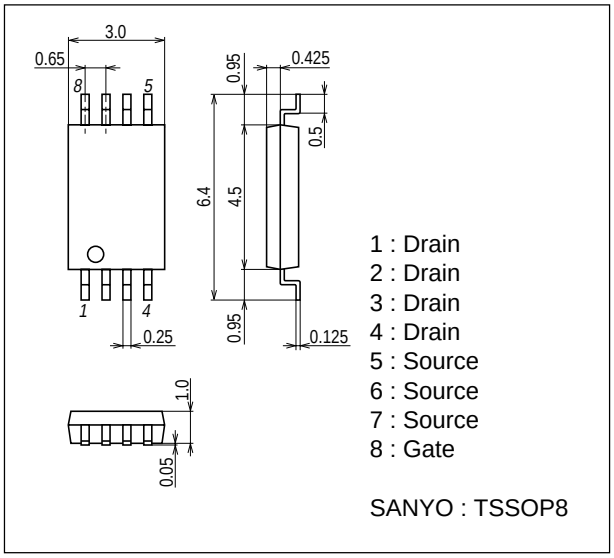
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		11		ns
Rise Time	t_r	See specified Test Circuit.		12		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		31		ns
Fall Time	t_f	See specified Test Circuit.		18		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=4.5A		8.5		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=4.5A		1.8		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=4.5A		1.3		nC
Diode Forward Voltage	V_{SD}	I_S=4.5A, V_{GS}=0V		0.85	1.2	V

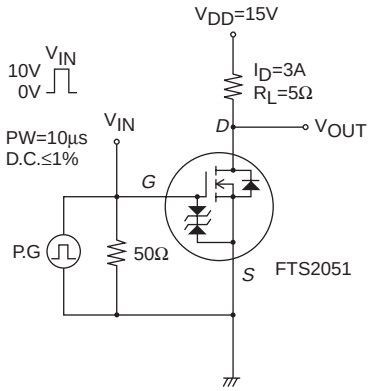
Package Dimensions

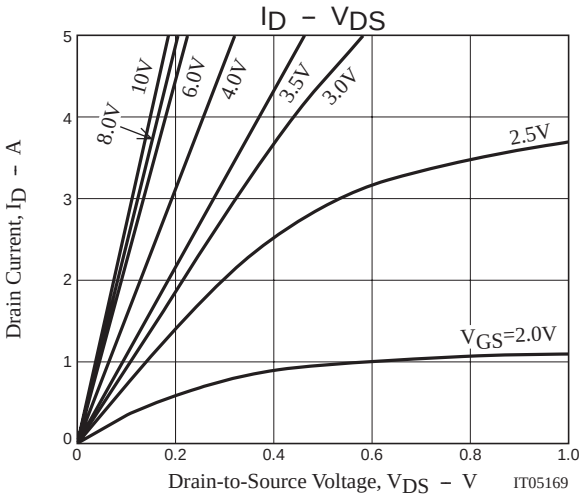
unit : mm

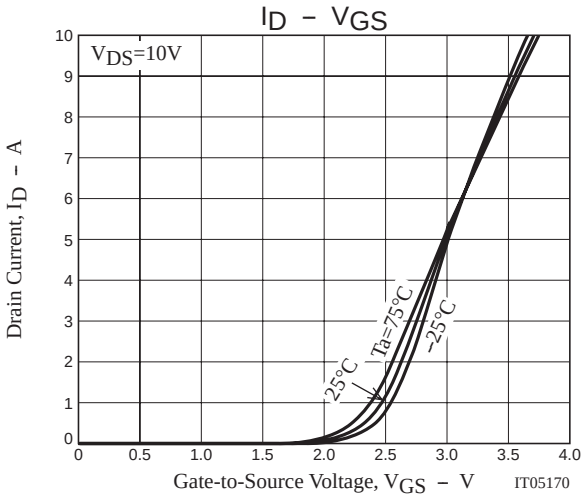
7006-008

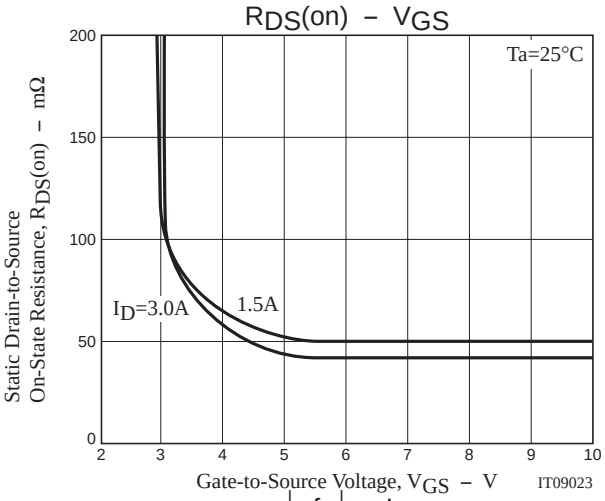


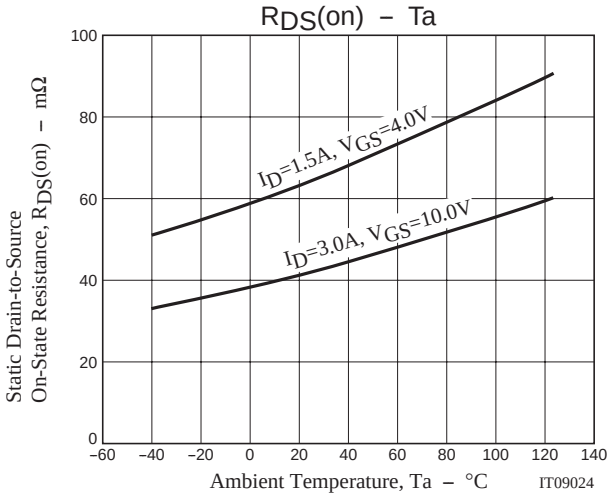
Switching Time Test Circuit

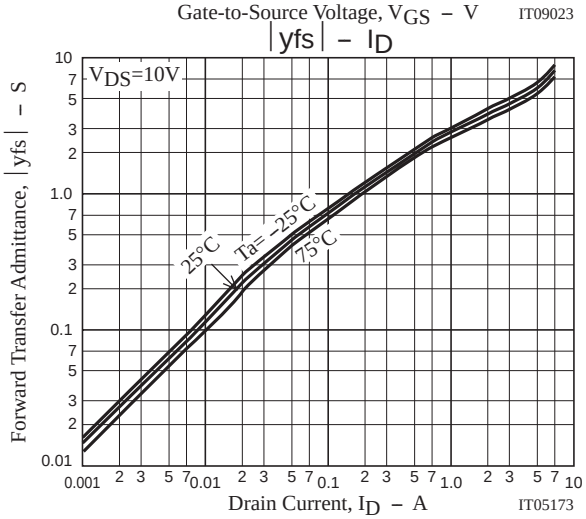


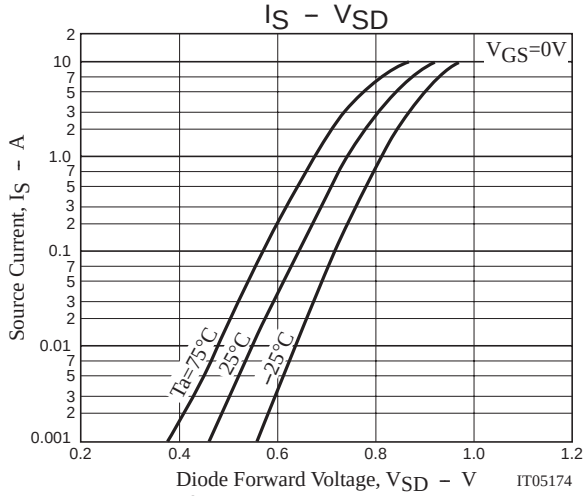


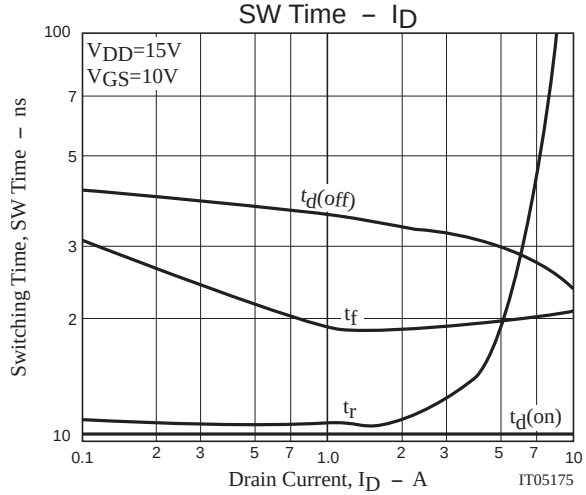


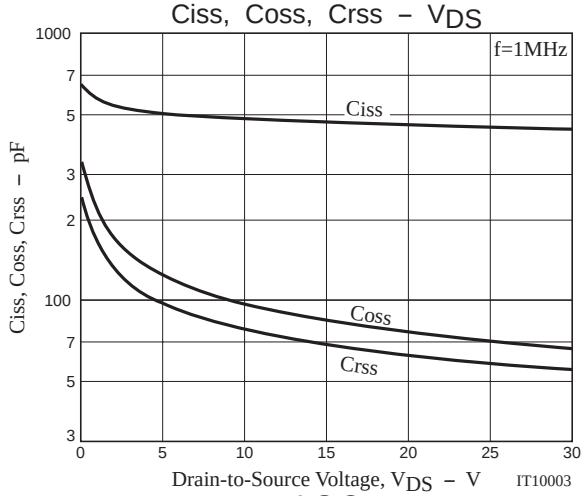

RDS(on) – VGS
Ta=25°C
ID=3.0A
1.5A
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Gate-to-Source Voltage, VGS – V
IT09023

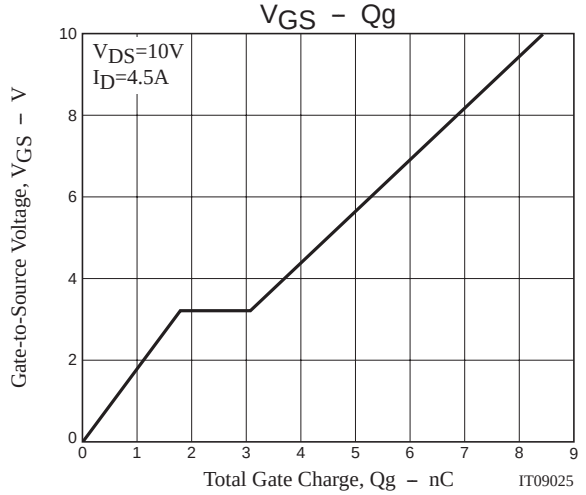

RDS(on) – Ta
ID=1.5A, VGS=4.0V
ID=3.0A, VGS=10.0V
Static Drain-to-Source On-State Resistance, RDS(on) – mΩ
Ambient Temperature, Ta – °C
IT09024

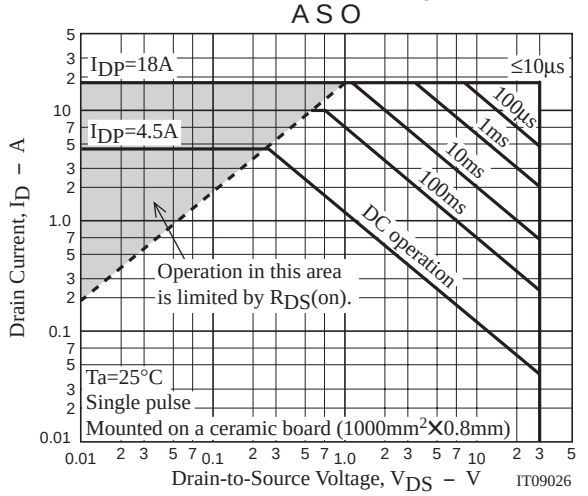

|yfs| – ID
VDS=10V
Ta=–25°C
25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT05173

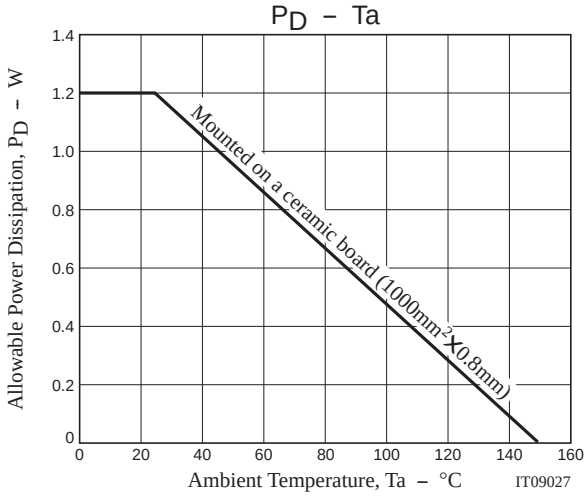

IS – VSD
VGS=0V
Ta=75°C
25°C
–25°C
Source Current, IS – A
Diode Forward Voltage, VSD – V
IT05174


SW Time – ID
VDD=15V
VGS=10V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT05175


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT10003


VGS – Qg
VDS=10V
ID=4.5A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT09025


ASO
IDP=18A
IDP=4.5A
≤10μs
100μs
1ms
10ms
100ms
DC operation
Operation in this area is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board (1000mm²×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT09026



Note on usage : Since the FTS2051 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.